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STATE KEY LABORATORY OF HIGH POWER SEMICONDUCTOR LASER OF CHANGCHUN UNIVERSITY OF SCIENCE AND TECHNOLOGY

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[教授/研究员](#)
魏志鹏

职 务:
职 称: 副教授

通讯地址: 吉林省长春市卫星路7186号科技大厦A座

联系电话: 0431-85583390

邮政编码: 130022

电子邮件: zhipengwei@gmail.com

简历

2000-至今 长春理工大学 教师

2002-2008 中科院长春光机物理所 博士

1996-2000 吉林大学 学士

研究领域

光电子材料与器件

学术兼职

主要荣誉

2012 吉林省创新拔尖人才, 吉林省科技进步三等奖

2011 中国仪器仪表学会奖学金·金国藩青年学子奖

2009 吉林省自然科学学术成果奖一等奖

2008 长白科技青年奖特优奖

吉林省科技进步一等奖

2007 中科院院长优秀奖

承担科研项目情况

教育部博士点基金1项, 归国留学人员基金1项, 实验室基金2项, 省科技厅基金项目1项, 省教育厅基础研究项目1项, 市科技局国际合作项目1项。

代表论著

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授权专利：

- 1.一种指导等离子体辅助制备半导体材料的光谱探测方法。专利号：ZL 200510016509.6